

isc Silicon NPN RF Transistor

2SC2734

DESCRIPTION

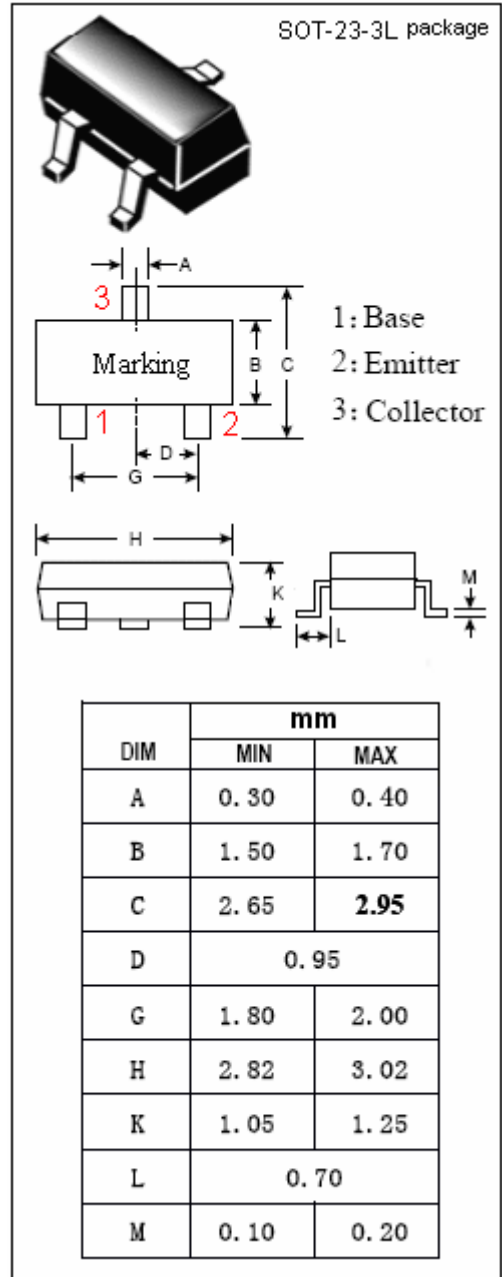
- Low Noise
- High Gain

APPLICATIONS

- UHF frequency converter
- Local oscillator , wide band amplifier

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	11	V
V _{EBO}	Emitter-Base Voltage	3	V
I _C	Collector Current-Continuous	50	mA
P _C	Collector Power Dissipation @T _C =25°C	0.15	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN RF Transistor

2SC2734

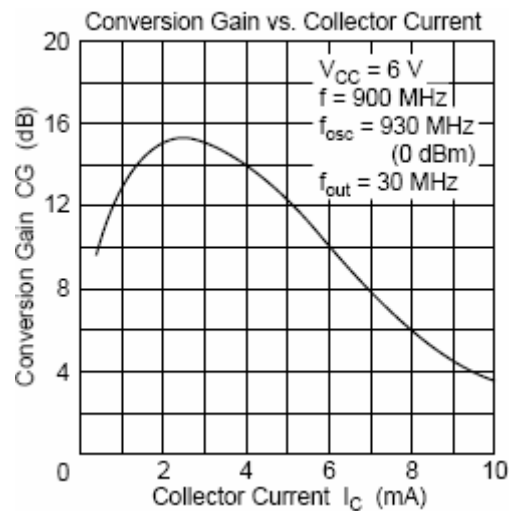
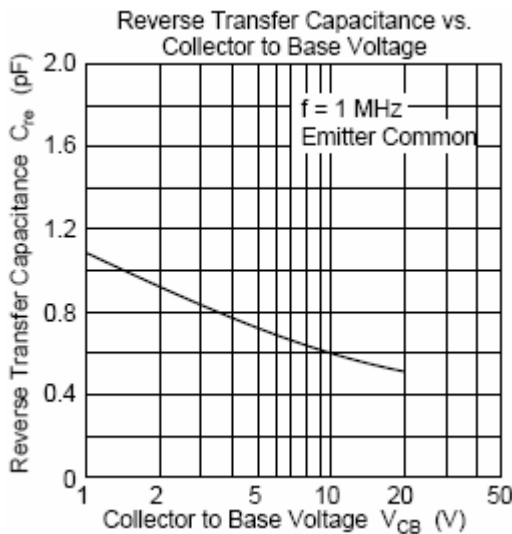
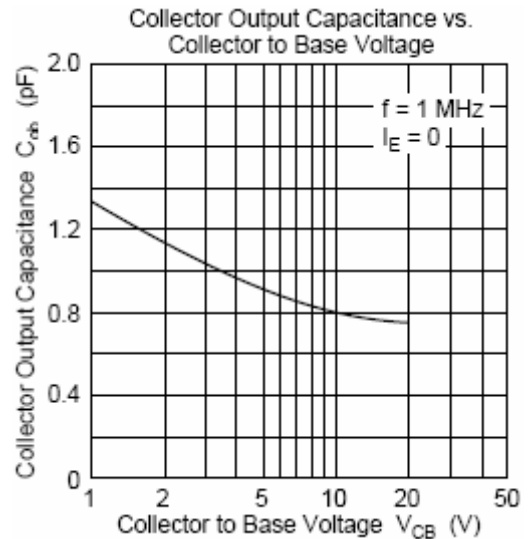
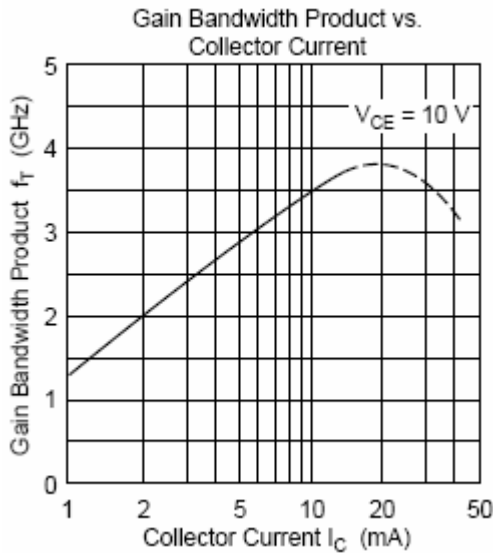
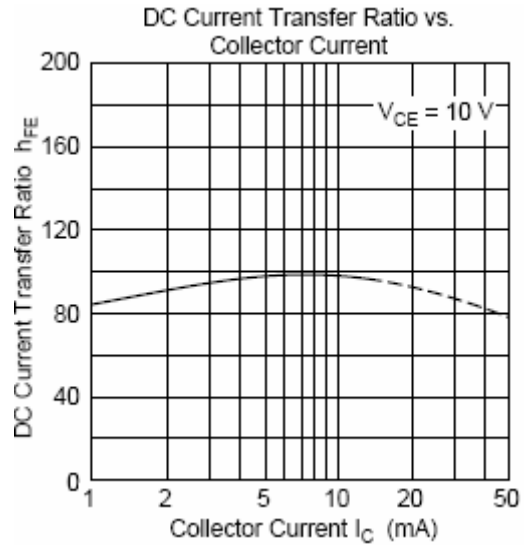
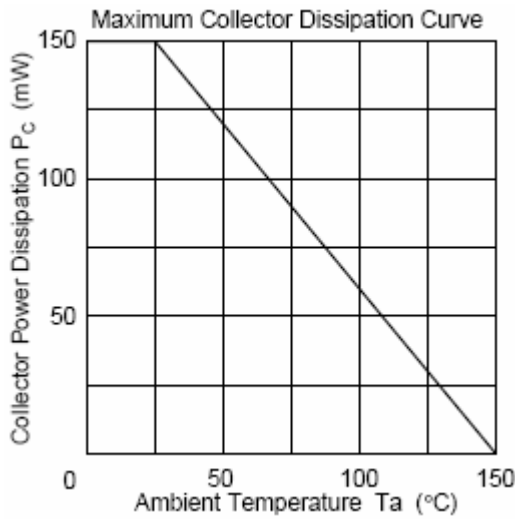
ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μ A ; I _E = 0	20			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1mA ; R _{BE} = ∞	11			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μ A ; I _C = 0	3			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA ; I _B = 5mA			0.7	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 10V ; I _E = 0			0.5	μ A
h _{FE}	DC Current Gain	I _C = 5mA ; V _{CE} = 10V	20		200	
f _T	Current-Gain—Bandwidth Product	I _C = 10mA ; V _{CE} = 10V	1.4	3.5		GHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V;f= 1.0MHz		0.9	1.5	pF
CG	Conversion Gain	I _C = 2mA ; V _{CC} = 6V;f= 900MHz f _{OSC} = 930MHz(0dBm), f _{out} = 30MHz		15		dB
NF	Noise Figure	I _C = 2mA ; V _{CC} = 6V;f= 900MHz f _{OSC} = 930MHz(0dBm), f _{out} = 30MHz		9		dB
V _{OSC}	Oscillating output voltage	I _C = 5mA ; V _{CC} = 6V;f= 930MHz		140		mV

isc Silicon NPN RF Transistor

2SC2734



isc Silicon NPN RF Transistor

2SC2734

